

Optocoupler, Phototransistor Output

Features

- Special construction:
Therefore, extra low coupling capacity of typical 0.2 pF, high **Common Mode Rejection**
- Low temperature coefficient of CTR
- Rated isolation voltage (RMS includes DC)
 $V_{IOWM} = 600 V_{RMS}$ (848 V peak)
- Rated recurring peak voltage (repetitive)
 $V_{IORM} = 600 V_{RMS}$
- Thickness through insulation ≥ 0.75 mm
- Creepage current resistance according to VDE 0303/IEC 60112
Comparative Tracking Index: CTI ≥ 275
- Rated impulse voltage (transient overvoltage)
 $V_{IOTM} = 6$ kV peak
- Isolation test voltage (partial discharge test voltage) $V_{pd} = 1.6$ kV

Agency Approvals

- UL 1577 Recognized, File No. E76222 - Double Protection
- BSI: BS EN 41003, BS EN 60095 (BS415), Certificate number 7081 and 7402
- DIN EN 60747-5-2(VDE0884)
DIN EN 60747-5-5 pending
- VDE related features:
- FIMKO (SETI): EN 60950, Certificate No. 12399

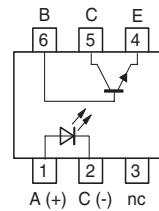
Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

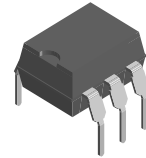
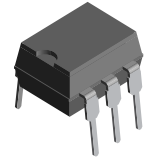
For appl. class I - IV at mains voltage ≤ 300 V

For appl. class I - III at mains voltage ≤ 600 V according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending, table 2, suitable for:

Switch-mode power supplies, line receiver, computer peripheral interface, microprocessor system interface.



17186



Order Information

| Part | Remarks |
|--------|--------------------------------------|
| 4N25GV | CTR > 20 % wide lead spacing, DIP-6 |
| 4N35GV | CTR > 100 % wide lead spacing, DIP-6 |
| 4N25V | CTR > 20 %, DIP-6 |
| 4N35V | CTR > 100 %, DIP-6 |

For additional order information see Option Section
G=Leadform 10.16 mm; G is not marked on the body

Description

The 4N25V/ 4N25GV/ 4N35V/ 4N35GV series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

The elements are mounted on one leadframe using a **coplanar technique**, providing a fixed distance between input and output for highest safety requirements.

Vishay Semiconductors

VDE Standards

These couplers perform safety functions according to the following equipment standards:

DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending

Optocoupler for electrical safety requirements

IEC EN 60950

Office machines (applied for reinforced isolation for mains voltage ≤ 400 VRMS)

VDE 0804

Telecommunication apparatus and data processing

IEC 60065

Safety for mains-operated electronic and related household apparatus

Absolute Maximum Ratings

$T_{amb} = 25$ °C, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

| Parameter | Test condition | Symbol | Value | Unit |
|-----------------------|-----------------------|------------|-------|------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | | I_F | 60 | mA |
| Forward surge current | $t_p \leq 10$ μ s | I_{FSM} | 3 | A |
| Power dissipation | | P_{diss} | 100 | mW |
| Junction temperature | | T_j | 125 | °C |

Output

| Parameter | Test condition | Symbol | Value | Unit |
|---------------------------|----------------------------------|------------|-------|------|
| Collector emitter voltage | | V_{CEO} | 32 | V |
| Emitter collector voltage | | V_{CEO} | 7 | V |
| Collector current | | I_C | 50 | mA |
| Collector peak current | $t_p/T = 0.5$, $t_p \leq 10$ ms | I_{CM} | 100 | mA |
| Power dissipation | | P_{diss} | 150 | mW |
| Junction temperature | | T_j | 125 | °C |

Coupler

| Parameter | Test condition | Symbol | Value | Unit |
|------------------------------|-------------------------------|-----------|---------------|-----------|
| Isolation test voltage (RMS) | $t = 1$ min | V_{ISO} | 3750 | V_{RMS} |
| Total power dissipation | | P_{tot} | 250 | mW |
| Ambient temperature range | | T_{amb} | - 55 to + 100 | °C |
| Storage temperature range | | T_{stg} | - 55 to + 125 | °C |
| Soldering temperature | 2 mm from case, $t \leq 10$ s | T_{sld} | 260 | °C |



Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|----------------------|-------------------------------|----------------|-----|------|-----|------|
| Forward voltage | I _F = 50 mA | V _F | | 1.2 | 1.4 | V |
| Junction capacitance | V _R = 0, f = 1 MHz | C _j | | 50 | | pF |

Output

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-----------------------------------|---|------------------|-----|------|-----|------|
| Collector emitter voltage | I _C = 1 mA | V _{CEO} | 32 | | | V |
| Emitter collector voltage | I _E = 100 μA | V _{ECO} | 7 | | | V |
| Collector-emitter leakage current | V _{CE} = 10 V, I _F = 0, T _{amb} = 100 °C | I _{CEO} | | | 50 | nA |
| | V _{CE} = 30 V, I _F = 0, T _{amb} = 100 °C | I _{CEO} | | | 500 | μA |

Coupler

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|--------------------------------------|---|--------------------|-----|------|-----|------|
| Collector emitter saturation voltage | I _F = 50 mA, I _C = 2 mA | V _{CEsat} | | | 0.3 | V |
| Cut-off frequency | V _{CE} = 5 V, I _F = 10 mA, R _L = 100 Ω | f _c | | 110 | | kHz |
| Coupling capacitance | f = 1 MHz | C _k | | 1 | | pF |

Current Transfer Ratio

| Parameter | Test condition | Part | Symbol | Min | Typ. | Max | Unit |
|--------------------------------|---|--------|--------|-----|------|-----|------|
| I _C /I _F | V _{CE} = 10 V, I _F = 10 mA | 4N25V | CTR | 20 | 100 | | % |
| | | 4N25GV | | | | | |
| | V _{CE} = 10 V, I _F = 10 mA, T _{amb} = 100 °C | 4N35V | CTR | 100 | 150 | | % |
| | | 4N35GV | | | | | |

Maximum Safety Ratings

(according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-5-5 pending) see figure 1

This optocoupler is suitable for safe electrical isolation only within the safety ratings.

Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

Input

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-----------------|----------------|----------------|-----|------|-----|------|
| Forward current | | I _F | | | 130 | mA |

Output

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-------------------|----------------|-------------------|-----|------|-----|------|
| Power dissipation | | P _{diss} | | | 265 | mW |

Coupler

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|-----------------------|----------------|------------|-----|------|-----|------|
| Rated impulse voltage | | V_{IOTM} | | | 6 | kV |
| Safety temperature | | T_{Si} | | | 150 | °C |

Insulation Rated Parameters

| Parameter | Test condition | Symbol | Min | Typ. | Max | Unit |
|---|---|------------|-----------|------|-----|----------|
| Partial discharge test voltage - Routine test | 100 %, $t_{test} = 1$ s | V_{pd} | 1600 | | | V |
| Partial discharge test voltage - Lot test (sample test) | $t_{Tr} = 60$ s, $t_{test} = 10$ s, (see figure 2) | V_{IOTM} | 6000 | | | V |
| | $t_{Tr} = 60$ s, $t_{test} = 10$ s, (see figure 2) | V_{pd} | 1300 | | | V |
| Insulation resistance | $V_{IO} = 500$ V | R_{IO} | 10^{12} | | | Ω |
| | $V_{IO} = 500$ V, $T_{amb} = 100$ °C | R_{IO} | 10^{11} | | | Ω |
| | $V_{IO} = 500$ V, $T_{amb} = 150$ °C (construction test only) | R_{IO} | 10^9 | | | Ω |

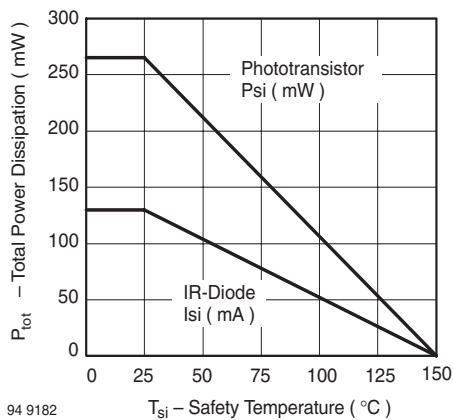


Figure 1. Derating diagram

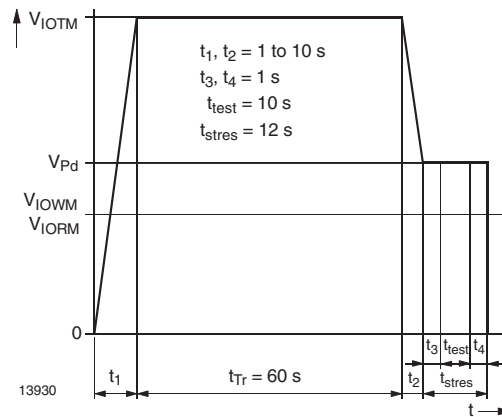


Figure 2. Test pulse diagram for sample test according to DIN EN 60747-5-2(VDE0884)/ DIN EN 60747-; IEC60747

Switching Characteristics

| Parameter | Test condition | Part | Symbol | Min | Typ. | Max | Unit |
|------------------------------|--|-----------------|-----------|-----|------|------|---------------|
| Delay time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_d | | 4.0 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_d | | 2.5 | | μs |
| Rise time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_r | | 7.0 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_r | | 3.0 | | μs |
| Fall time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_f | | 6.7 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_f | | 4.2 | | μs |
| Storage time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_s | | 0.3 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_s | | 0.3 | | μs |
| Turn-on time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_{on} | | 11.0 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_{on} | | | 10.0 | μs |
| Turn-off time (see figure 3) | $V_S = 5\text{ V}, I_C = 5\text{ mA}, R_L = 100\ \Omega$ | 4N25V 4N25GV | t_{off} | | 7.0 | | μs |
| | $V_S = 5\text{ V}, I_C = 2\text{ mA}, R_L = 100\ \Omega$ | 4N35V 4N35GV | t_{off} | | | 10.0 | μs |
| Turn-on time (see figure 4) | $V_S = 5\text{ V}, I_F = 10\text{ mA}, R_L = 1\text{ k}\Omega$ | 4N25V 4N25GV | t_{on} | | 25.0 | | μs |
| | | 4N35V 4N35GV | t_{on} | | 9.0 | | μs |
| Turn-off time (see figure 4) | $V_S = 5\text{ V}, I_F = 10\text{ mA}, R_L = 1\text{ k}\Omega$ | 4N25V 4N25GV | t_{off} | | 42.5 | | μs |
| | | 4N35V 4N35GV | t_{off} | | 25.0 | | μs |

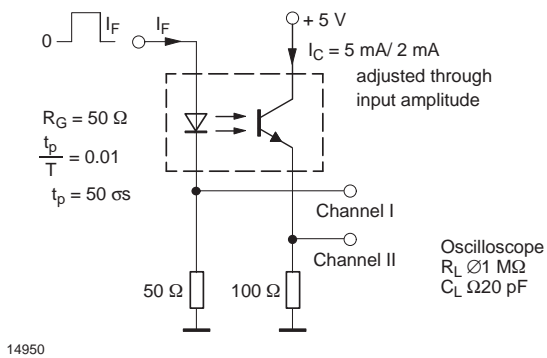


Figure 3. Test circuit, non-saturated operation

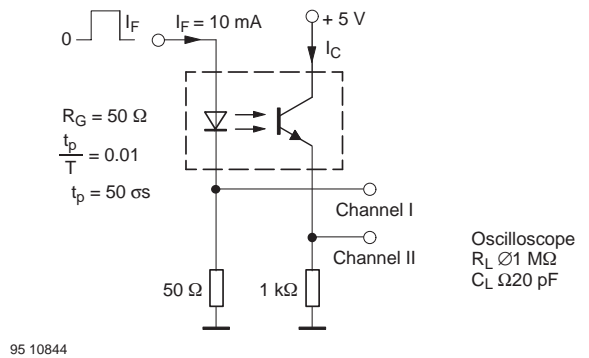


Figure 4. Test circuit, saturated operation

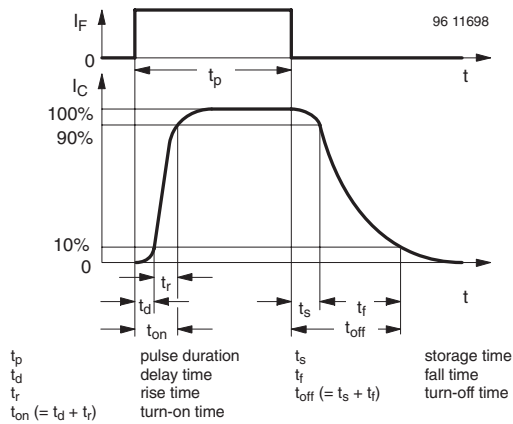


Figure 5. Switching times

Typical Characteristics ($T_{amb} = 25^\circ\text{C}$ unless otherwise specified)

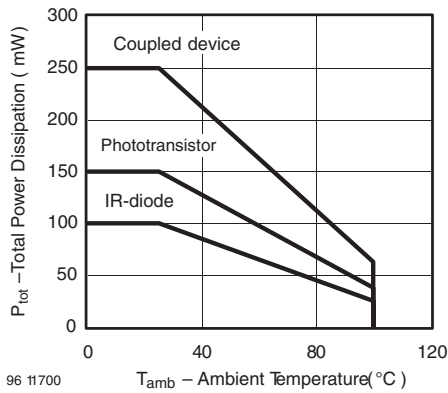


Figure 6. Total Power Dissipation vs. Ambient Temperature

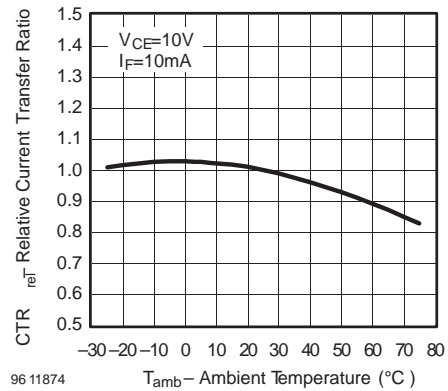


Figure 8. Relative Current Transfer Ratio vs. Ambient Temperature

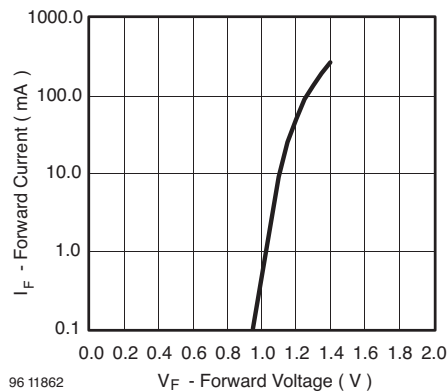


Figure 7. Forward Current vs. Forward Voltage

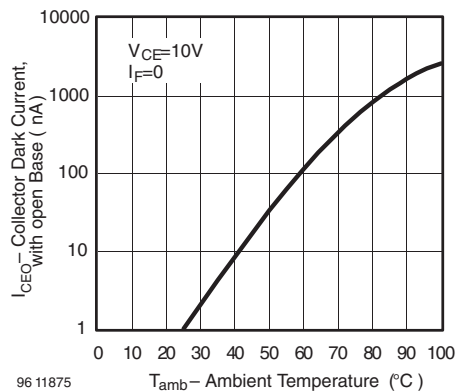


Figure 9. Collector Dark Current vs. Ambient Temperature

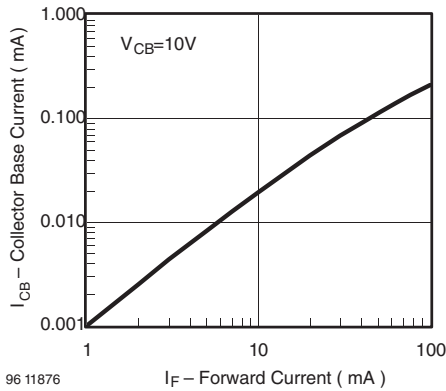


Figure 10. Collector Base Current vs. Forward Current

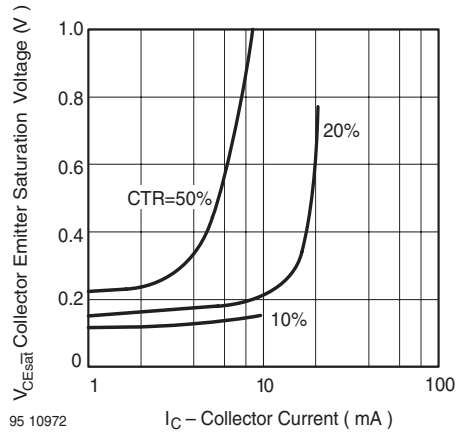


Figure 13. Collector Emitter Saturation Voltage vs. Collector Current

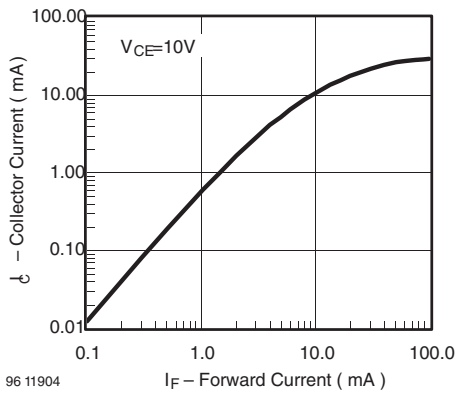


Figure 11. Collector Current vs. Forward Current

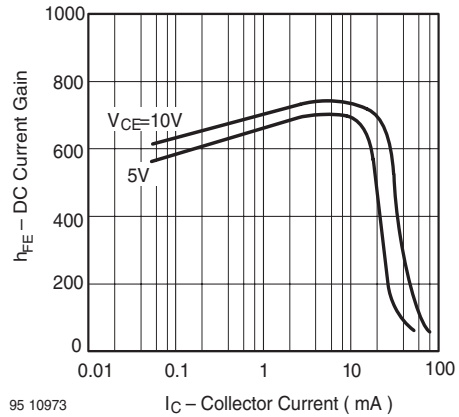


Figure 14. DC Current Gain vs. Collector Current

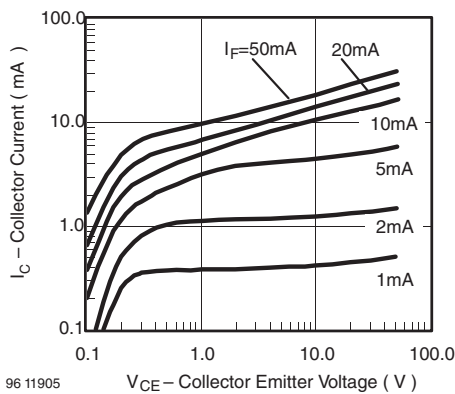


Figure 12. Collector Current vs. Collector Emitter Voltage

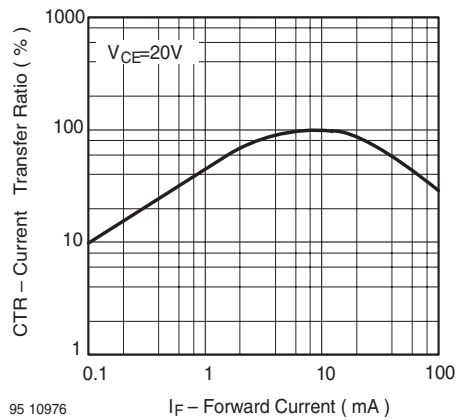


Figure 15. Current Transfer Ratio vs. Forward Current

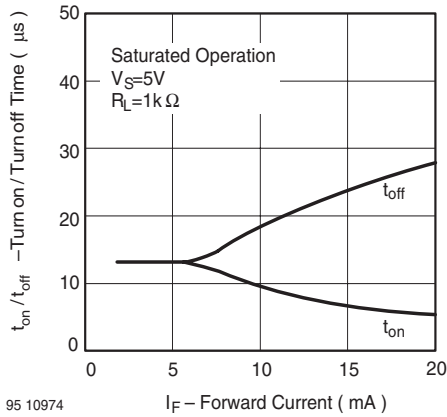


Figure 16. Turn on / off Time vs. Forward Current

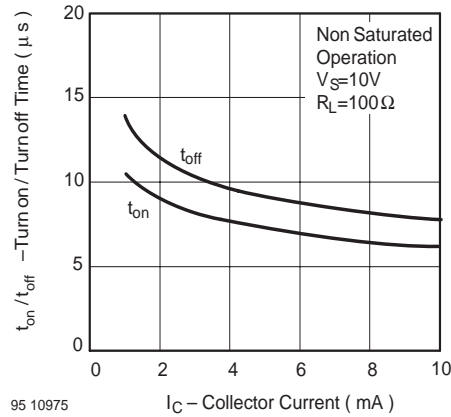
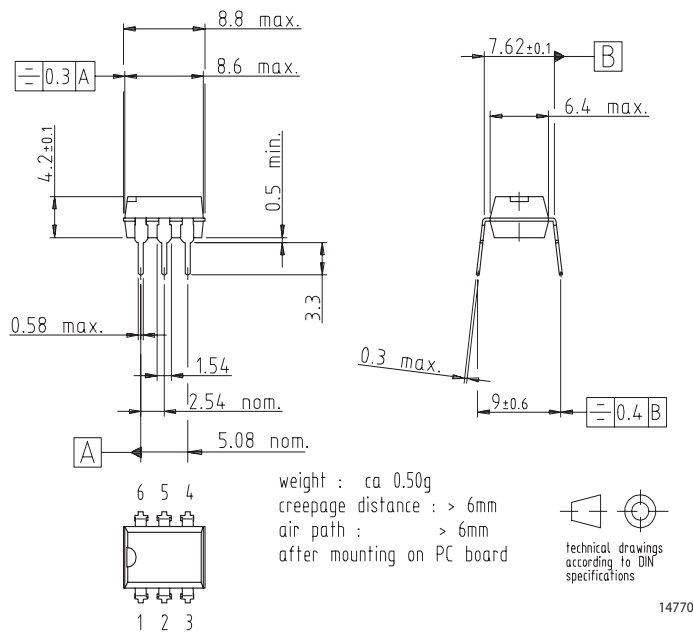
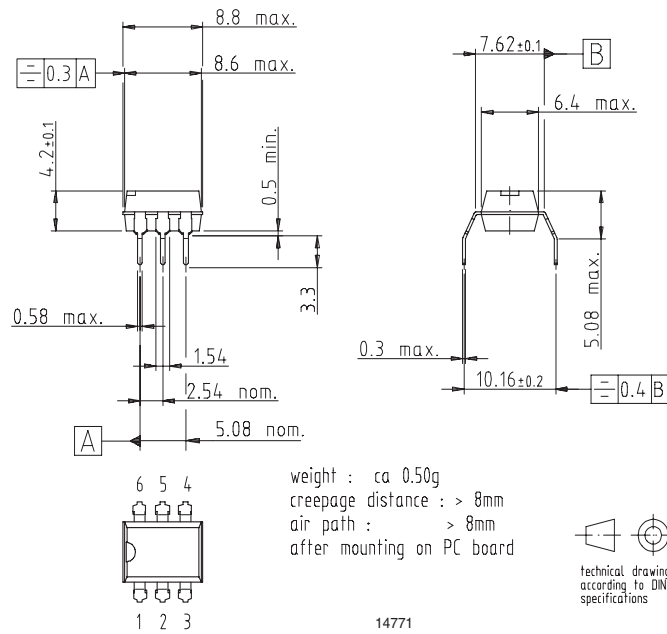


Figure 17. Turn on / off Time vs. Collector Current

Package Dimensions in mm



Package Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423